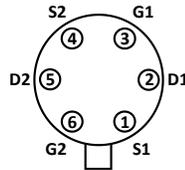
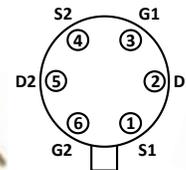


### LOW INPUT CAPACITANCE MONOLITHIC DUAL N-CHANNEL JFET

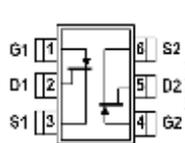
| FEATURES   |                                       |
|--|---------------------------------------|
| Ultra-Low Noise  | $e_n=2.5nV/\sqrt{Hz}$ @1kHz TYP.      |
| Low Leakage  | $I_G=15pA$ TYPs.                      |
| Low Drift  | $ V_{GS1-2}/T =5\mu V/^{\circ}C$ max. |
| Ultra-Low Offset Voltage                                     | $ V_{GS1-2} =1mV$ max.                |
| ABSOLUTE MAXIMUM RATINGS <sup>1</sup>                        |                                       |
| @ 25°C (unless otherwise noted)                              |                                       |
| Maximum Temperatures   |                                       |
| Storage Temperature  | -55° to +150°C                        |
| Operating Junction Temperature                               | -55° to +150°C                        |
| Maximum Voltage and Current for Each Transistor <sup>1</sup> |                                       |
| -V <sub>GSS</sub>  | Gate Voltage to Drain or Source 60V   |
| I <sub>G(f)</sub>  | Gate Forward Current 50mA             |
| Maximum Power Dissipation <sup>2</sup>                       |                                       |
| Device Dissipation <sup>2</sup> @ Free Air - Total           | 400mW T <sub>A</sub> =+25°C           |



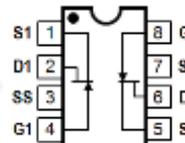
TO-71 6L  
Top View



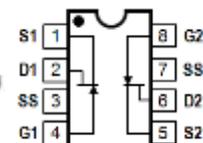
TO-78 6L  
Top View



SOT-23 6L  
Top View



SOIC-A 8L  
Top View



PDIP 8L  
Top View

\* For equivalent single version, see LSK189

### Features

- Low Noise:  $e_n = 2.5nV/\sqrt{Hz}$  (typ),  $f = 1kHz$ , NBW = 1Hz
- Very Low Common Source Input Capacitance of  $C_{ISS} = 3pF$  – typ and 8pF- max
- High Slew Rate
- Low Offset/Drift Voltage
- Low Gate Leakage  $I_{GSS}$  and  $I_G$
- High CMRR 102 dB

### Benefits

- Tight Differential Voltage Match vs. Current
- Improved Op Amp Speed Settling Time Accuracy
- Minimum Input Error Trimming Error Voltage
- Lower Intermodulation Distortion

### Applications

- Wideband Differential Amplifiers
- High Speed Temperature Compensated Single Ended Input Amplifier Amps
- High Speed Comparators
- Impedance Converters
- Sonobouys and Hydrophones
- Acoustic Sensors

### Description

The LS844 Series is the industry's lowest input capacitance and low-noise monolithic dual N-Channel JFET. Low input capacitance substantially reduces intermodulation distortion. In addition, these dual JFETs feature tight offset voltage and low drift over temperature range, and are targeted for use in a wide range of precision instrumentation and sensor applications.

The LS844 Series is available in surface mount plastic SOIC 8L, PDIP 8L and SOT-23 6L packages. Additionally, it is offered in thru-hole metal cans; the TO-71 6L and TO-78 6L package.

For an equivalent single N-Channel version refer to the LSK189 datasheet. LS844 Series TO-71 6L and SOIC 8L are fit, form and pin compatible to the same LSK389 product.

The LS844 Series provides an increase in capabilities for a wide range of low-noise applications.

The most significant aspect of the LS844 Series is how it combines a noise level comparable with the LSK389 while having much lower gate-to-drain capacitance, 4pF versus the 25pF. The slightly higher noise of the LS844 Series, versus the LSK389, is not significant in most instances, while the much lower capacitance enables designers to produce simpler, more elegant circuit designs with fewer devices that cost less in production.

Like the Linear Systems LSK389, the LS844 Series features a unique design construction of interleaving both JFETs on the same piece of silicon to provide excellent matching and thermal tracking, as well as a low-noise profile having nearly zero popcorn noise.

**Electrical Characteristics @ 25°C (unless otherwise noted)**

| SYMBOL                 | CHARACTERISTIC        | LS843 | LS844 | LS845 | UNITS                        | CONDITIONS  |
|------------------------|-----------------------|-------|-------|-------|------------------------------|---|
| $I_{V_{GS1-2}/T}$ max. | Drift vs. Temperature | 5     | 10    | 25    | $\mu\text{V}/^\circ\text{C}$ | $V_{DG} = 10\text{V}$ $I_D = 500\mu\text{A}$<br>$T_A = -55^\circ\text{C}$ to $+125^\circ\text{C}$ |
| $I_{V_{GS1-2}}$ max.   | Offset Voltage        | 1     | 5     | 15    | mV                           | $V_{GS} = 10\text{V}$ $I_D = 500\mu\text{A}$  |

| SYMBOL                    | CHARACTERISTIC                               | MIN.     | TYP. | MAX. | UNITS         | CONDITIONS  |
|---------------------------|--|----------|------|------|---------------|---|
| $BV_{GSS}$                | Breakdown Voltage                            | -60      | --   | --   | V             | $V_{DS} = 0$ $I_D = -1\text{nA}$  |
| $BV_{GGO}$                | Gate-to-Gate Breakdown                       | $\pm 60$ | --   | --   | V             | $I_{GGO} = \pm 1\mu\text{A}$ $I_D = 0$ $I_S = 0$                        |
| $G_{fss}$                 | <b>TRANSCONDUCTANCE</b><br>Full Conduction   | 1500     | --   | --   | $\mu\text{S}$ | $V_{DS} = 15\text{V}$ $V_{GS} = 0$ $f = 1\text{kHz}$                    |
| $G_{fs}$                  | Typical Conduction                           | 1000     | 1500 | --   | $\mu\text{S}$ | $V_{DS} = 15\text{V}$ $I_D = 500\mu\text{A}$                            |
| $ G_{fs1-2}/G_{fs1} $     | Mismatch                                     | --       | 0.6  | 3    | %             |   |
| $I_{DSS}$                 | <b>DRAIN CURRENT</b><br>Full Conduction      | 1.5      | 5    | 15   | mA            | $V_{DS} = 15\text{V}$ $V_{GS} = 0$                                      |
| $ I_{DSS1-2}/I_{DSS} $    | Mismatch at Full Conduction                  | --       | 1    | 5    | %             |   |
| $V_{GS}(\text{off})$      | <b>GATE VOLTAGE</b><br>Pinchoff Voltage      | -1       | --   | -3.5 | V             | $V_{DS} = 15\text{V}$ $I_D = 1\text{nA}$                                |
| $V_{GS}$                  | Operating Range                              | -0.5     | --   | -3.5 | V             | $V_{DS} = 15\text{V}$ $I_D = 500\mu\text{A}$                            |
| $-I_G$                    | <b>GATE CURRENT</b><br>Operating             | --       | 15   | 50   | pA            | $V_{DG} = 15\text{V}$ $I_D = 500\mu\text{A}$                            |
| $-I_G$                    | High Temperature                             | --       | --   | 50   | nA            | $V_{DG} = 15\text{V}$ $I_D = 500\mu\text{A}$ $T_A = +125^\circ\text{C}$ |
| $-I_G$                    | Reduced VDG                                  | --       | 5    | 30   | pA            | $V_{DG} = 3\text{V}$ $I_D = 500\mu\text{A}$                             |
| $-I_{GSS}$                | At Full Conduction                           | --       | --   | 100  | pA            | $V_{GS} = 15\text{V}$ $V_{GS} = 0$                                      |
| $G_{OSS}$                 | <b>OUTPUT CONDUCTANCE</b><br>Full Conduction | --       | --   | 40   | $\mu\text{S}$ | $V_{DS} = 15\text{V}$ $V_{GS} = 0$                                      |
| $G_{OS}$<br>$ G_{OS1-2} $ | Operating<br>Differential                    | --       | 2.0  | 2.7  | $\mu\text{S}$ | $V_{DS} = 15\text{V}$ $I_D = 200\mu\text{A}$                            |
|                           |  | --       | 0.02 | 0.2  | $\mu\text{S}$ |   |

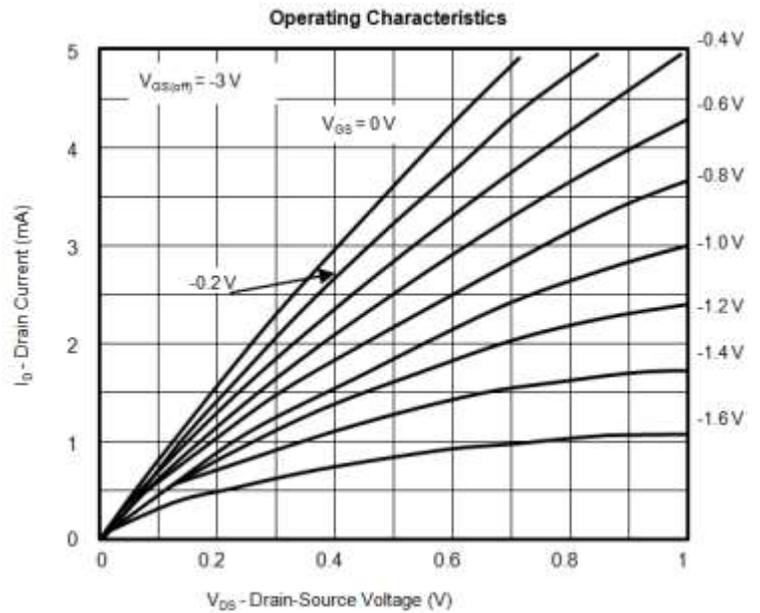
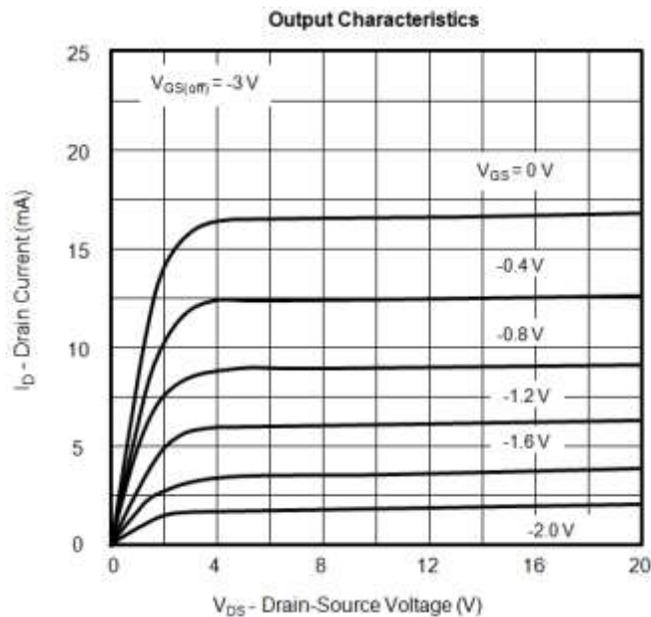
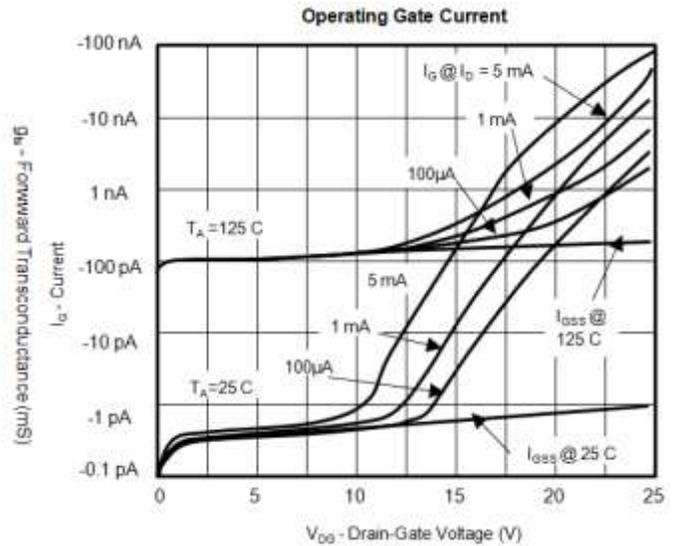
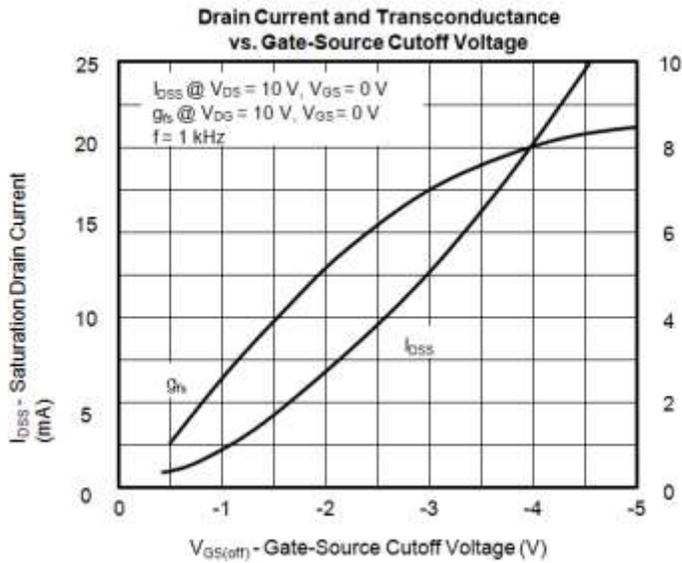
| SYMBOL    | CHARACTERISTIC   | MIN. | TYP. | MAX. | UNITS | CONDITIONS   |
|-----------|--|------|------|------|-------|--|
|           | <b>COMMON MODE REJECTION</b>                                     |      |      |      |       |  |
| CMRR      | $-20 \log \left  \frac{\Delta V_{GS1-2}}{\Delta V_{DS}} \right $ | 90   | 100  | --   | dB    | $V_{DS} = 10 \text{ to } 20\text{V}$ $I_D = 500\mu\text{A}$              |
| CMRR      |  | --   | 85   | --   | dB    | $V_{DS} = 5 \text{ to } 10\text{V}$ $I_D = 500\mu\text{A}$               |
| $e_n$     | Voltage  | --   | --   | 3.0  | nV/Hz | $V_{DS} = 15\text{V}$ $I_D = 2.0\text{mA}$ $f = 1\text{kHz}$<br>NBW= 1Hz |
| $e_n$     | Voltage  | --   | --   | 7.0  | nV/Hz | $V_{DS} = 15\text{V}$ $I_D = 2.0\text{mA}$ $f = 10\text{Hz}$<br>NBW= 1Hz |
|           | <b>CAPACITANCE</b>   |      |      |      |       |  |
| $C_{ISS}$ | Input  | --   | --   | 8    | pF    | $V_{DS} = 15\text{V}$ $I_D = 500\mu\text{A}$ $f = 1\text{mHz}$           |
| $C_{RSS}$ | Reverse Transfer   | --   | --   | 3    | pF    |  |
| $C_{DD}$  | Drain-to-Drain   | --   | 0.5  | --   | pF    | $V_{DD} = 15\text{V}$ $I_D = 500\mu\text{A}$ $f = 1\text{mHz}$           |

**Notes:**

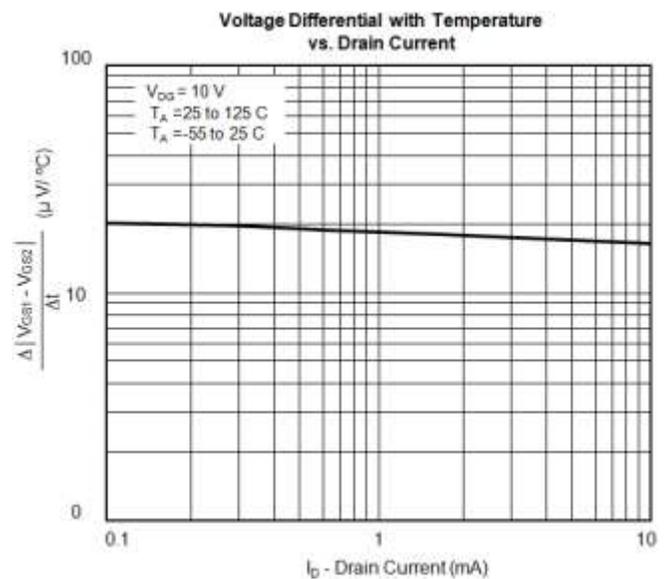
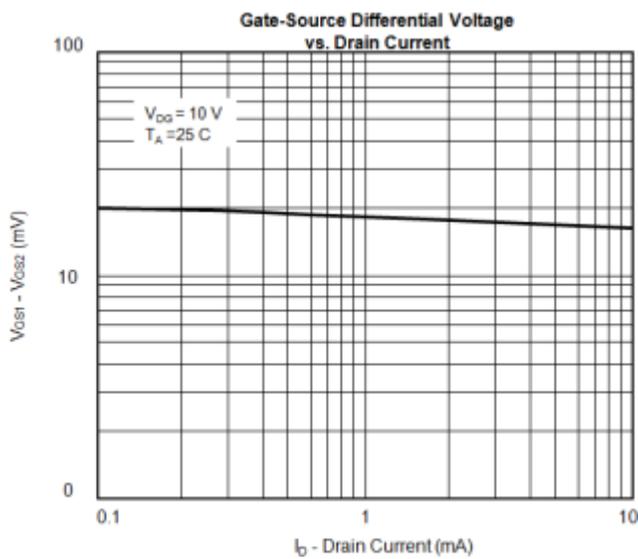
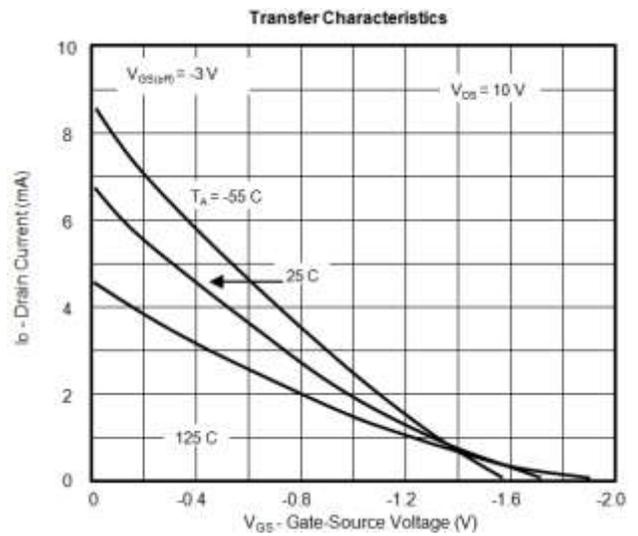
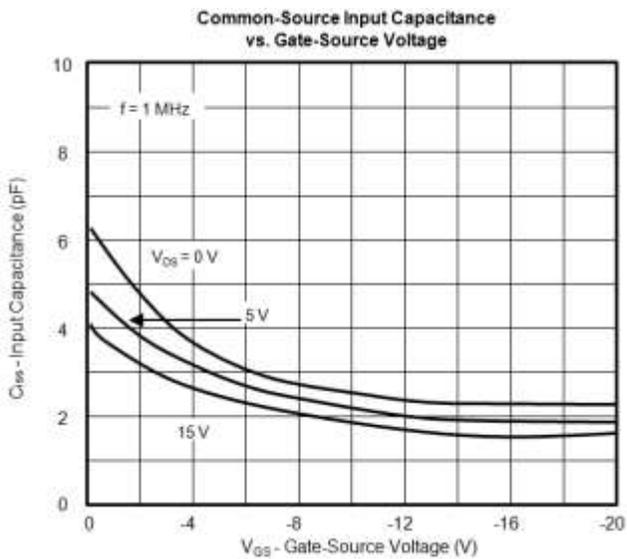
1. Absolute maximum ratings are limiting values above which serviceability may be impaired.
2. Pulse width  $\leq 2\text{ms}$ .
3. All MIN/TYP/MAX Limits are absolute values. Negative signs indicate electrical polarity only.
4. Derate 2.4 mW/°C above 25°C.
5. Derate 4 mW/°C above 25°C.

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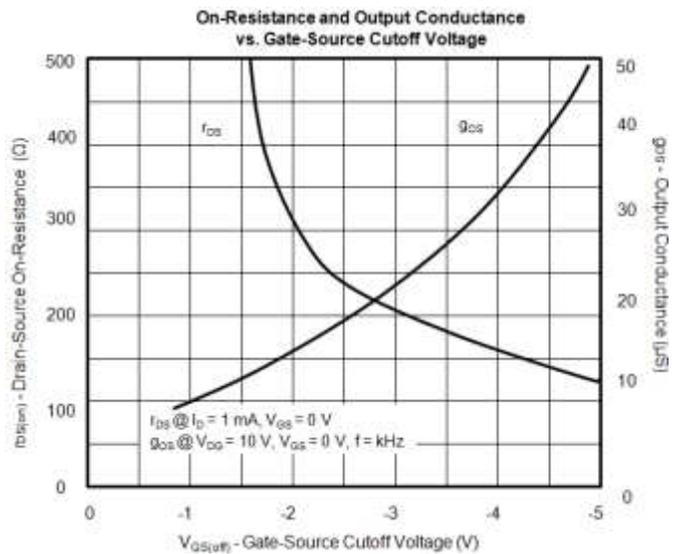
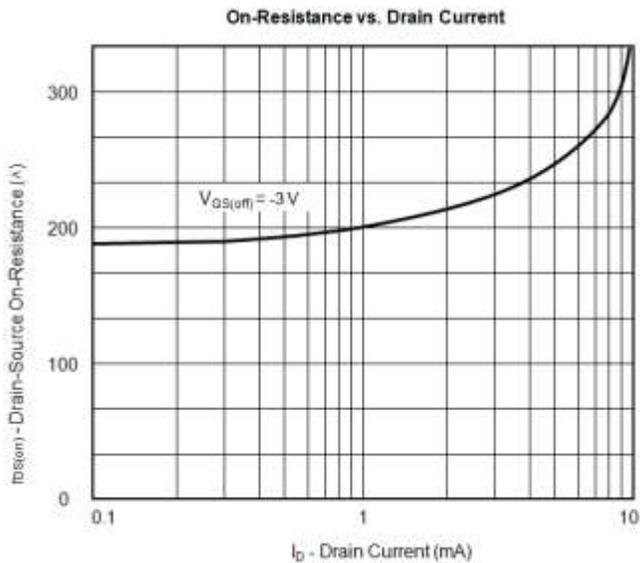
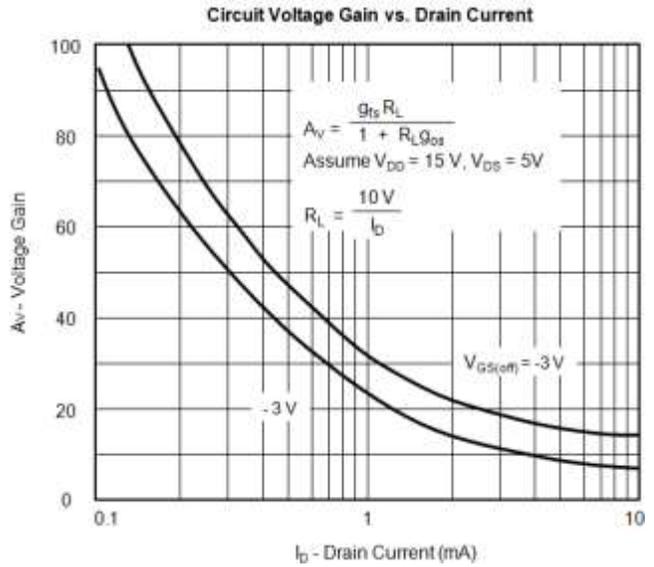
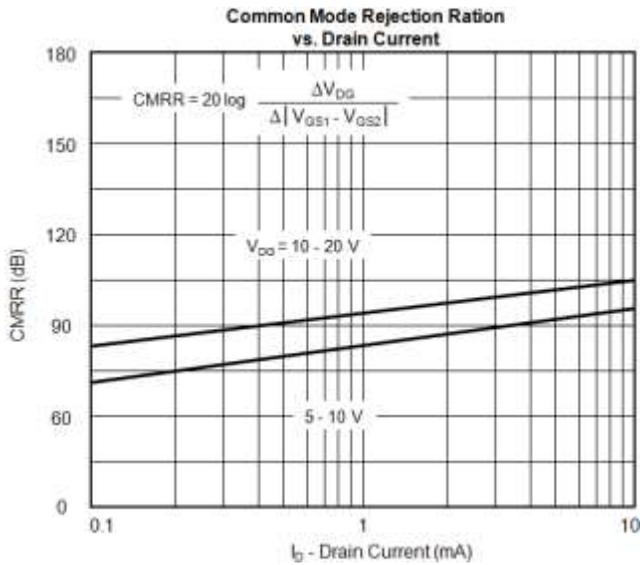
## Typical Characteristics



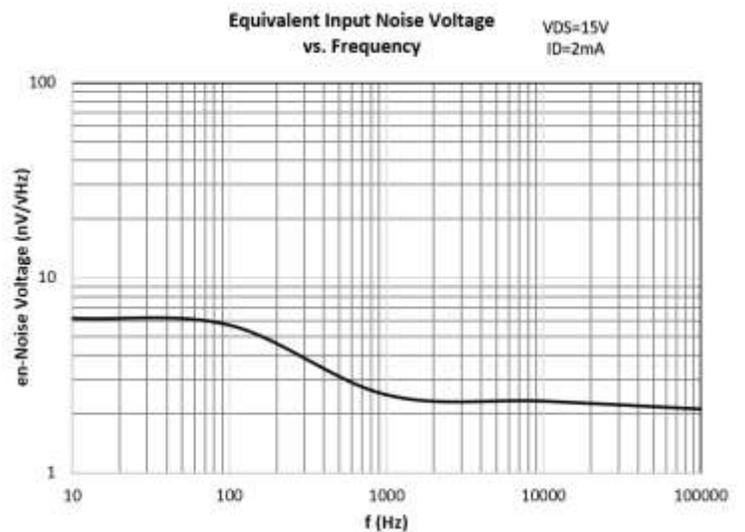
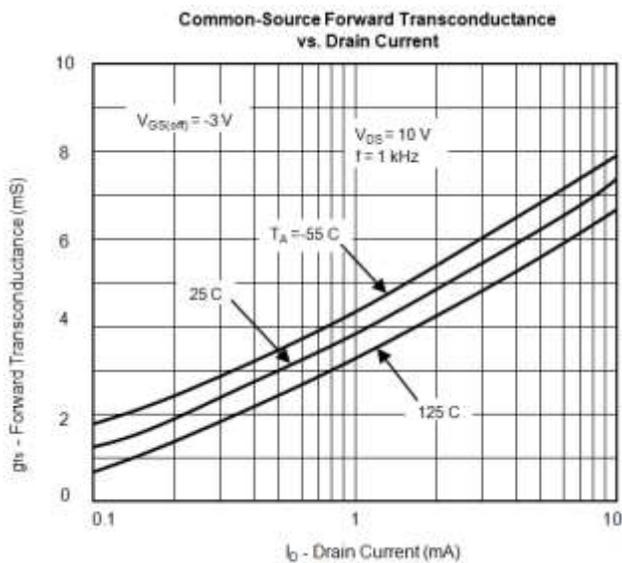
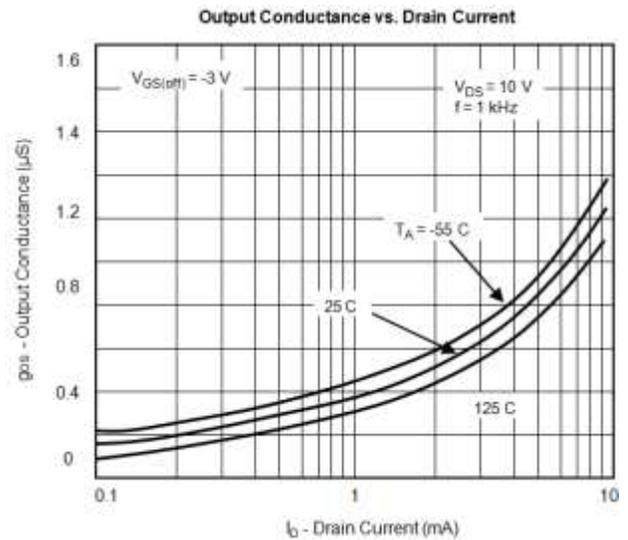
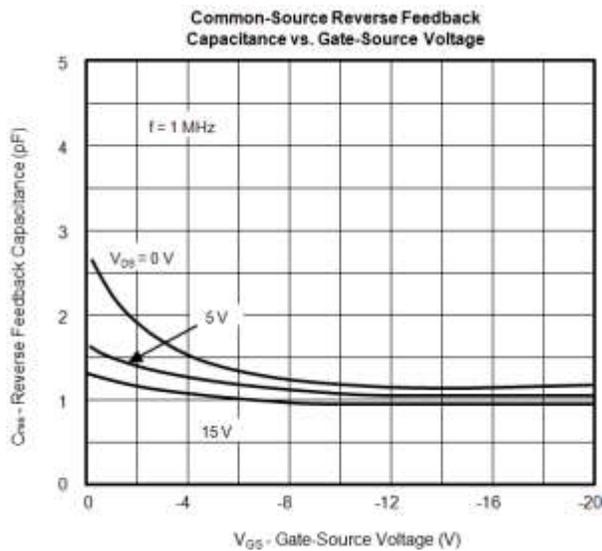
## Typical Characteristics Continued



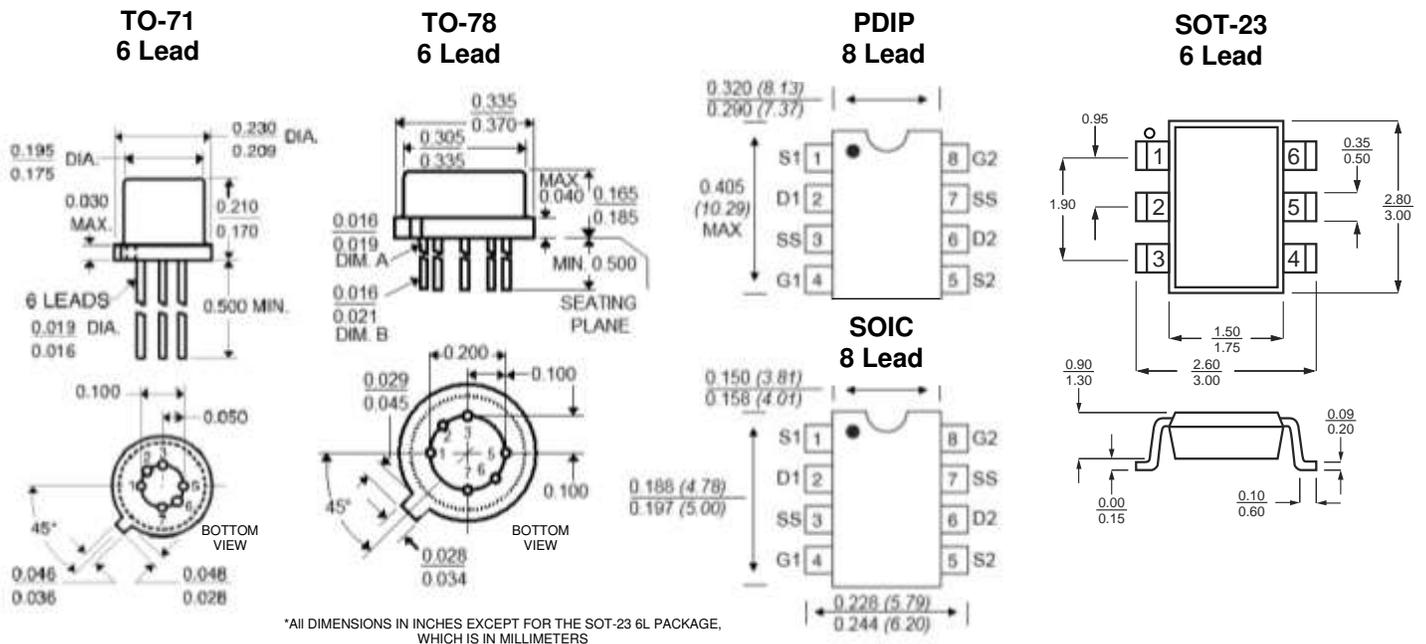
## Typical Characteristics Continued



## Typical Characteristics Continued



Package Dimensions:



Ordering Information:

| Standard Part Call-Out   |                              |                              |
|--|------------------------------|------------------------------|
| LS843 TO-71 6L RoHS  | LS844 TO-71 6L RoHS          | LS845 TO-71 6L RoHS          |
| LS843 TO-78 6L RoHS  | LS844 TO-78 6L RoHS          | LS845 TO-78 6L RoHS          |
| LS843 SOT-23 6L RoHS   | LS844 SOT-23 6L RoHS         | LS845 SOT-23 6L RoHS         |
| LS843 SOIC 8L RoHS   | LS844 SOIC 8L RoHS           | LS845 SOIC 8L RoHS           |
| LS843 PDIP 8L RoHS   | LS844 PDIP 8L RoHS           | LS845 PDIP 8L RoHS           |
| Custom Part Call-Out (Custom Parts Include SEL + 4 Digit Numeric Code) |                              |                              |
| LS843 TO-71 6L RoHS SELXXXX  | LS844 TO-71 6L RoHS SELXXXX  | LS845 TO-71 6L RoHS SELXXXX  |
| LS843 TO-78 6L RoHS SELXXXX  | LS844 TO-78 6L RoHS SELXXXX  | LS845 TO-78 6L RoHS SELXXXX  |
| LS843 SOT-23 6L RoHS SELXXXX   | LS844 SOT-23 6L RoHS SELXXXX | LS845 SOT-23 6L RoHS SELXXXX |
| LS843 SOIC 8L RoHS SELXXXX   | LS844 SOIC 8L RoHS SELXXXX   | LS845 SOIC 8L RoHS SELXXXX   |
| LS843 PDIP 8L RoHS SELXXXX   | LS844 PDIP 8L RoHS SELXXXX   | LS845 PDIP 8L RoHS SELXXXX   |